

# P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)	
- 100	$0.250 \text{ at V}_{GS} = -10 \text{ V}$	- 8.8	11.7	
- 100	$0.280$ at $V_{GS} = -4.5 \text{ V}$	- 8.0	11.7	

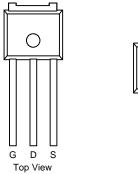
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested Compliant to RoHS Directive 2002/95/EC

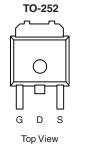


#### **APPLICATIONS**

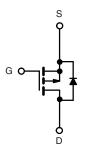
- · Power Switch
- DC/DC Converters



TO-251



Drain Connected to Tab



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>C</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 100	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current /T 150 °C)	T <sub>C</sub> = 25 °C	I-	- 8.8		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	l <sub>D</sub>	- 7.1	A	
Pulsed Drain Current	I <sub>DM</sub>	- 25			
Avalanche Current	I <sub>AS</sub>	- 18			
Single Avalanche Energy <sup>a</sup> L = 0.1 mH		E <sub>AS</sub>	16.2	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	32.1 <sup>b</sup>	10/	
	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_D$ $-$	2.5	- W	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	50	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	3.9	C/VV		

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$					V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 2.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		0.250	0.279	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.4 A		0.280	0.350		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3.6 A		12		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1055		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 50 V, f = 1 MHz		65			
Reverse Transfer Capacitance	C <sub>rss</sub>	]		41			
Total Cata Charge <sup>C</sup>	Qg	V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		23.2	34.8	nC	
Total Gate Charge <sup>c</sup>				11.7	17.6		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.6 \text{ A}$		3.5			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			4.8			
Gate Resistance	$R_g$	f = 1 MHz	1.2	5.7	11.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			7	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -50 \text{ V}, R_L = 17.2 \Omega$		12	18	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 2.9 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		33	50	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	]		9	18	1	
Drain-Source Body Diode Ratings a	nd Characteri	stics T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 8.8	۸	
Pulsed Current	I <sub>SM</sub>				- 15	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = - 2.9 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			50	75	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	1		98	147	nC	

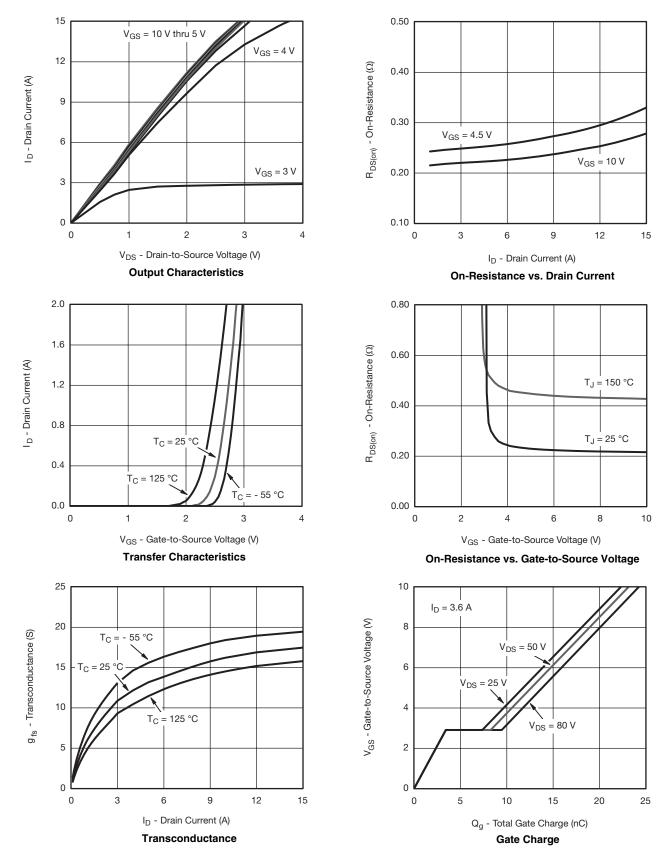
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

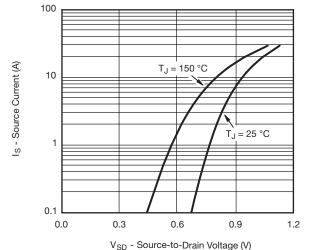


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

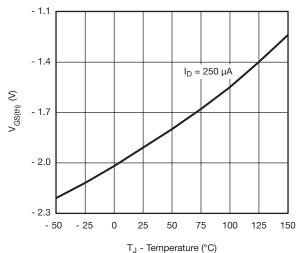




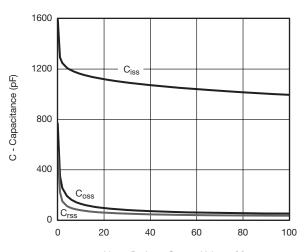
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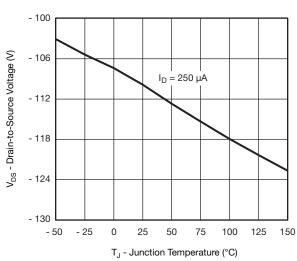
Source-Drain Diode Forward Voltage



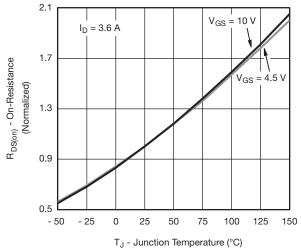
Threshold Voltage



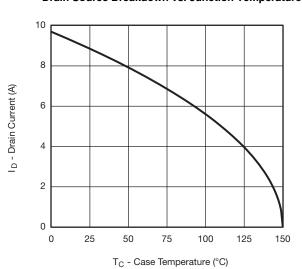
 $V_{DS}$  - Drain-to-Source Voltage (V)  $\label{eq:capacitance}$ 



**Drain Source Breakdown vs. Junction Temperature** 



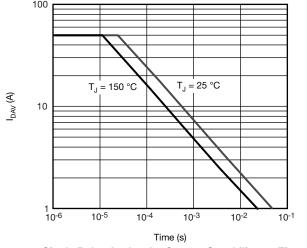
On-Resistance vs. Junction Temperature

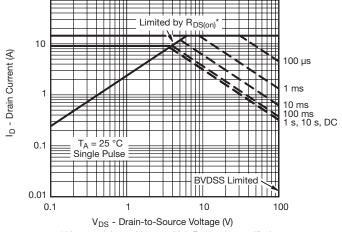


**Current Derating** 

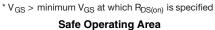


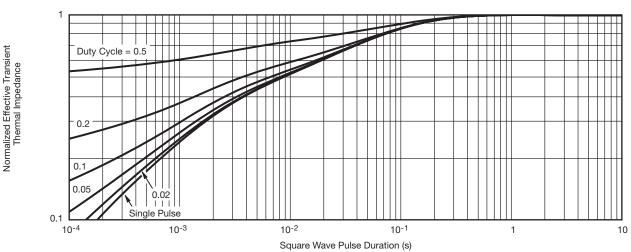
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Avalanche Current Capability vs. Time

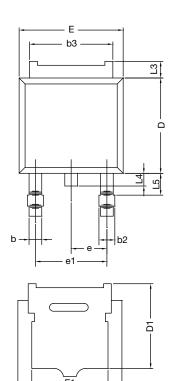


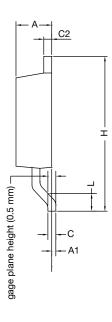


Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-252AA Case Outline**





	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
Е	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28 BSC 0.090 BSC			BSC
e1	4.56 BSC		0.180	BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16				

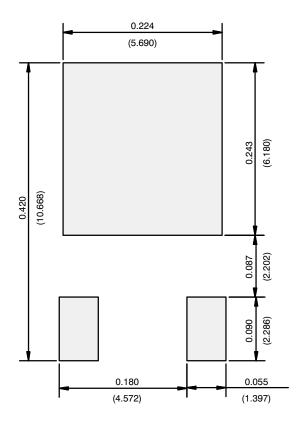
ECN: T16-0236-Rev. P, 16-May-DWG: 5347

#### Notes

• Dimension L3 is for reference only.



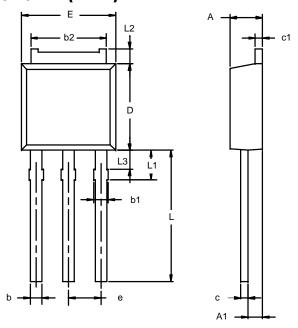
## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)



## TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIMETERS INCHE			HES
Dim	Min	Max	Min	Max
Α	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
С	0.46	0.58	0.018	0.023
с1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
Е	6.48	6.73	0.255	0.265
е	2.28	BSC	0.090	BSC
L	8.89	9.53	0.350	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346				



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